SDB310Q

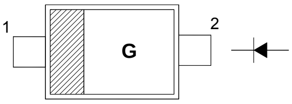
SCHOTTKY BARRIER DIODE

Features

- Low power rectified
- Silicon epitaxial type
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**G**"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Current	I_F	0.2	A
Repetitive Peak Forward Current	I_{FRM}	0.5	A
Non-Repetitive Peak Forward Current (10 ms)	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 10 mA at I_F = 30 mA	V_F	 0.4 0.5	V
Reverse Current at V_R = 30 V	I_R	1	µA
Total Capacitance at V_R = 1 V, f = 1 MHz	C_T	10	pF
Reverse Recovery Time at $I_F = I_R$ = 10 mA, I_{RR} = 1 mA, R_L = 100 Ω	t_{rr}	5	ns

Fig. 1 I_F-V_F

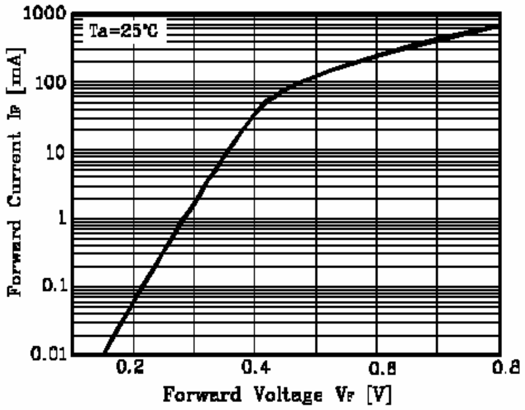


Fig. 2 I_R -V_R

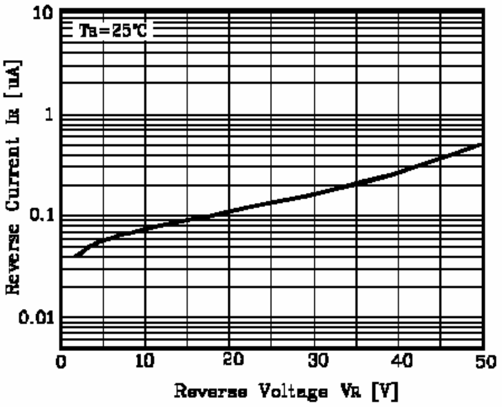
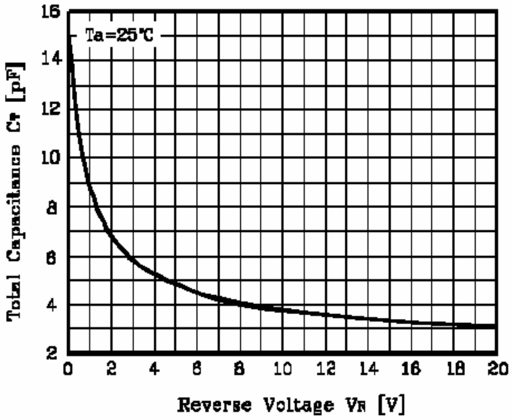
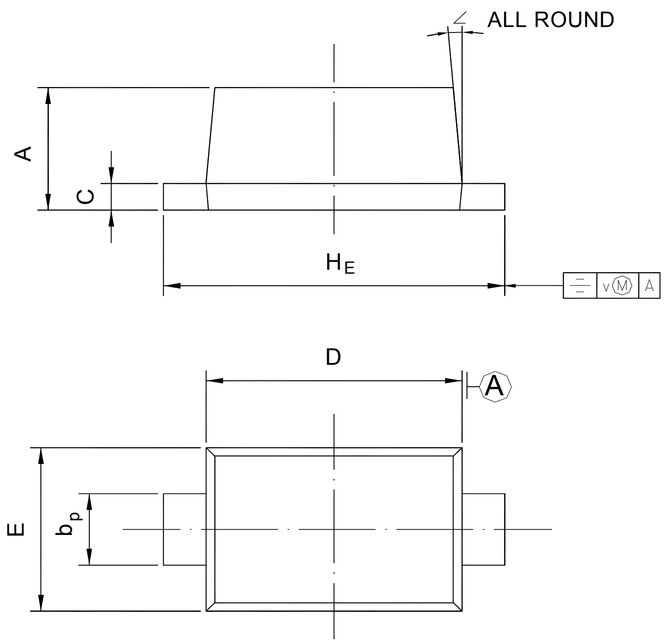


Fig. 3 C_T-V_R



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.127	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°